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The impact of process optimization on planar THz-Schottky device reliability

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Abstract

The technological complexity as well as space-application quality standards require sophisticated process control and optimization for reliability improvement of planar THz-Schottky devices. Degradation mechanisms are initiated using, the Transmission Line Pulse (TLP)-method and monitored as a function of the number of applied pulses. The degradation analysis is performed by IV-measurements on the one side and by Transmission electron microscopy (TEM) on the other side.